



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

FAST SWITCHING DIODE

VOLTAGE 50 Volts CURRENT 200 mAmpere

LL4150PT

Lead free devices

APPLICATION

- * Extreme fast switches.

FEATURE

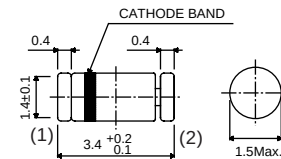
- * Small surface mounting type. (MINI-MELF)
- * High speed. ($T_{RR}=4.0\text{ns}$ Typ.)
- * Suitable for high packing density.
- * Maximum total power dissipation is 500mW.

CONSTRUCTION

- * Silicon epitaxial planar



Mini-Melf



Dimensions in millimeters

Mini-Melf

CIRCUIT



MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

RATINGS	SYMBOL	LL4150PT	UNITS
Peak Reverse Voltage	V_{RM}	50	Volts
Reverse Voltage	V_R	50	Volts
Repetitive Peak Forward Current	I_F	200	mAmps
Average Forward Current	I_{FAV}	200	mAmps
Peak Forward Surge Current @ $t=1.0\mu\text{s}$	I_{FSM}	0.5	Amps
Power Dissipation at $T_A=25^\circ\text{C}$	P_{tot}	500	mWatt
Maximum Capacitance (Note 1)	C_{tot}	4.0	pF
Maximum Reverse Recovery Time (Note 2)	T_{RR}	4.0	nS
Operating Temperature Range	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	LL4150PT	UNITS
Maximum Instantaneous Forward Voltage	V_F	1.0	Volts
Maximum Average Reverse Current at Reverse Voltage, $V_R=50\text{V}$	@ $T_A = 25^\circ\text{C}$	0.1	μAmps
	@ $T_J = 150^\circ\text{C}$	100	μAmps
Reverse Breakdown Voltage at $I_R=5\text{mA}$	V_{br}	35(min.)	Volts

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volt.
2. $I_F=-I_R=10$ to 200mA, to 0.1I_F

2007-04

RATING CHARACTERISTIC CURVES (LL4150PT)

FIG. 1 - FORWARD CHARACTERISTICS

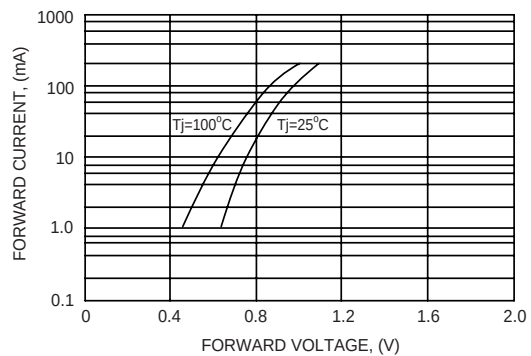


FIG. 2 - REVERSE CHARACTERISTICS

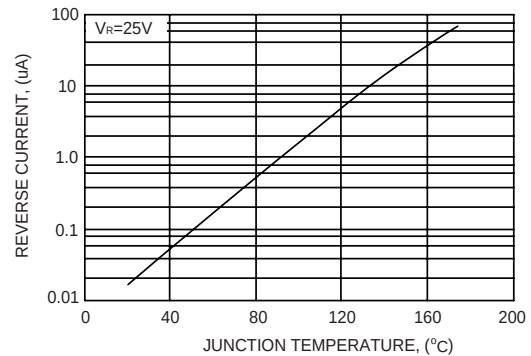


FIG. 3 - DIODE CAPACITANCE

